

In the Specification:

Please amend the paragraph beginning on page 12, line 7 as follows:

First, the silicon substrate 15 shown in Figs. 5A through 5C is prepared. In this silicon substrate 15, ~~anisotropic~~ anisotropic etching is performed on the upper surface of the substrate consisting of silicon single crystal, thereby forming a substantially V-shaped (trapezoidal) first groove portion 15b. The inclination angle (θ_1 , θ_2 , and θ_3) of the first through third inclined surfaces 15e, 15f and 15g are all 54.7 degrees.